

2N1595 - 2N1596 - 2N1597 - 2N1598 - 2N1599

SILICON THYRISTORS

Industrial-type, low-current silicon controlled rectifiers in a three-lead package ideal for printed-circuit applications Current handling capability of 1.6 amperes at junction temperetures to 100°C. Compliance to RoHS.

MAXIMUM RATINGS (*)

T_J=100°C unless otherwise noted

Symbol	Ratings	2N1595	2N1596	2N1597	2N1598	2N1599	Unit
V _{RSM(REP)}	Peak reverse blocking voltage (*)	50	100	200	300	400	V
I _{T(RMS)}	Forward Current RMS (all conduction angles)			1.6			А
I _{TSM}	Peak Surge Current (One Cycle, 60Hz, T _J =-20 to+100°C)			15			А
P _{GM}	Peak Gate Power – Forward			0.1			W
P _{G(AV)}	Average Gate Power - Forward			0.01			W
I _{GM}	Peak Gate Current – Forward			0.1			А
V _{GFM}	Peak Gate Voltage - Forward			10			V
V _{GRM}	Peak Gate Voltage - Reverse			10			V
TJ	Operating Junction Temperature Range		-	20 to +10	C		ംറ
T _{STG}	Storage Temperature Range		-	20 to +120	C		0



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ELECTRICAL CHARACTERISTICS

 $T_J\!=\!25^\circ C$ unless otherwise noted, $R_{GK}\!=\!1000\Omega$

Symbol	Ratings		2N1595	2N1596	2N1597	2N1598	2N1599	Unit
V _{DRM}	Peak Forward Blocking Voltage *	Min :	50	100	200	300	400	V
I _{RRM}	Peak Reverse Blocking Cu (Rated V _{DRM} , T _J =100°C)	urrent			Max 1			mA
I _{DRM}	Peak Forward Blocking Cu (Rated V_{DRM} with gate open $T_J = 100^{\circ}$ C)				Max 1			mA
I _{GT}	Gate Trigger Current Anode Voltage=7.0 Vdc, R	L=12Ω		Тур	: 2.0, Max	: 10		mA
V _{GT}	Gate Trigger Voltage Anode Voltage=7.0 Vdc, R	L=12Ω		Тур	: 0.7, Max	: 3.0		V
¥GI	V_{DRM} = Rated, R _L =100 Ω , T _J =100°C				Min : 0.2			v
I _H	Holding Current Anode Voltage=7.0 Vdc, gate open				Тур : 5.0			mA
V _{TM}	Forward On Voltage I _T =1 Adc			Тур	: 1.1, Max	: 2.0		V
t _{gt}	Turn-On Time (t _d +t _r) I _{GT} =10 mA, I _T =1 A				Тур : 0.8			μS
t _q	Turn-Off Time $I_T=1 A$, $I_R=1 A$, $dv/dt=20 V$ $T_J=100^{\circ}C$ $V_{DRM} = Rated Voltage$	/μs,			Тур : 10			μS

(*) V_{DRM} or V_{RSM} can be applied for all types on a continuous dc basis without incurring damage.

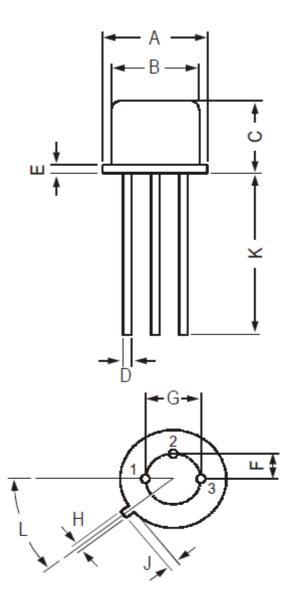


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MECHANICAL DATA CASE TO-39

DIMENSIONS (mm)		
	min max	
А	8.50	9.39
В	7.74	8.50
С	6.09	6.60
D	0.40	0.53
E	-	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
К	12.70	-
L	42°	48°

1: kathode	Pin 1 :
n 2 : Gate	Pin 2 :
n 3 : Anode	Pin 3 :
se : anode	Case :



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